

UTT50P10

Preliminary

-50A, -100V P-CHANNEL POWER MOSFET

DESCRIPTION

The UTC **UTT50P10** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance. It can also withstand high energy in the avalanche.

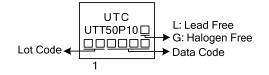
FEATURES

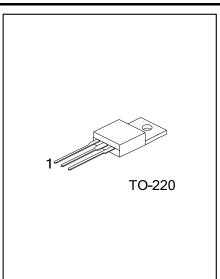
- * V_{DS}= -100V
- * I_D = -50A
- * $R_{DS(ON)}$ < 60m Ω @ V_{GS} = -10V, I_D = -20A
- * High Switching Speed

ORDERING INFORMATION

Ordering Number			Daakaga	Pin Assignment			Deaking		
Lead Free	Halogen Free		Package	1 2 3		3	Packing		
UTT50P10L-TA3-T	UTT50P10G-TA3-T		TO-220	G	D	S	Tube		
Note: Pin Assignment: G: Gate D: Drain S: Source									
UTT50P10L-TA3-T (1)Packing Type (2)Package Type		(1) T: Tube (2) TA3: TO-220							
(3)Green Package			(3) L: Lead Free, G: Halogen Free and Lead Free						

MARKING





■ ABSOLUTE MAXIMUM RATINGS (T_c=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Gate-Source Voltage		V _{GSS}	±20	V
Drain Current	Continuous	I _D	-50	А
	Pulsed	I _{DM}	-90	А
Power Dissipation		PD	225	W
Junction Temperature		ТJ	+150	°C
Storage Temperature		T _{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θ _{JC}	0.55	°C/W

ELECTRICAL CHARACTERISTICS

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV_{DSS}	I _D =-250μA, V _{GS} =0V				V	
Drain-Source Leakage Current		I _{DSS}	V _{DS} =0.8×Max.rating, V _{GS} =0V, T _J =25°C			-1	1	
			V _{DS} =0.8×Max.rating, V _{GS} =0V, T _J =125°C			-500	μA	
Gate- Source Leakage	Forward		V _{GS} =+20V			+100	nA	
Current	Reverse	I _{GSS}	V _{GS} =-20V			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		V _{GS(TH)}	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1		-3	V	
Static Drain-Source On-State Resistance		Recon	V _{GS} =-10V, I _D =-20A			60	mΩ	
			V _{GS} =-4.5V, I _D =-15A			65	mΩ	
DYNAMIC PARAMETERS								
Input Capacitance Output Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =-50V, f=1.0MHz		4200		pF	
		C _{OSS}			250		pF	
Reverse Transfer Capacitance		C _{RSS}			110		pF	
SWITCHING PARAMETERS								
Turn-ON Delay Time		t _{D(ON)}			80	130	ns	
Rise Time		t _R	V _{DD} =-50V, V _{GS} =-10V, I _D =-50A, R _G =1Ω		76	130	ns	
Turn-OFF Delay Time		t _{D(OFF)}	VDD30V, VGS10V, ID30A, IXG-132		740	900	ns	
Fall-Time		t _F			200	400	ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Drain-Source Diode Forward Voltage	V _{SD}	I _F =-20A, V _{GS} =0V, Pulse test, t≤300µs,	-1.0	-1.5	v			
	a voltage		duty cycle d≤2%	1.0	1.0	v		
Body Diode Reverse Recovery Time		t _{RR}	T _J =25°C, I _F =-20A, V _R =-50V,	80	120	ns		
			di/dt=-100A/µs	00				



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

